Excellent Integrated System Limited

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STMicroelectronics TD310IDT

For any questions, you can email us directly: sales@integrated-circuit.com





TRIPLE IGBT/MOS DRIVER WITH CURRENT SENSE

- THREE POWER IGBT/MOS AND PULSE TRANSFORMER DRIVERS
- CURRENT SENSE COMPARATOR
- UNCOMMITTED OP-AMP
- 0.6 A PER CHANNEL PEAK OUTPUT CURRENT CAPABILITY
- LOW OUTPUT IMPEDANCE TYP: 7Ω AT 200mA
- CMOS/LSTTL COMPATIBLE INVERTING INPUT WITH HYSTERESIS
- 4V TO 16V SINGLE SUPPLY OPERATION
- LOW BIAS CURRENT TYP: 1.5mA
- ADJUSTABLE UNDERVOLTAGE LOCKOUT **LEVEL**
- STAND-BY MODE
- CHANNEL PARALLELING CAPABILITY

DESCRIPTION

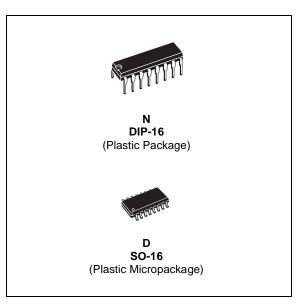
The TD310 is designed to drive one, two or three Power IGBT/MOS and has driving capability for pulse transformer. So it is perfectly suited to interface control IC with Power Switches in low side or half-bridge configuration.

TD310 includes a current sense comparator which inhibit the output drivers in case of overcurrent. An alarm output signals the even to a controller.

TD310 also includes an uncommitted op-amp which can be used for current measurement (as an amplifier before the A/D input of a microcontroller) of for other general purpose.

Programmable undervoltage lockout and standby mode make TD310 suitable for a large area of environment and application.

Typical applications are low side IGBT and power MOSFET drive in three phase systems, pulse transformer drive, and general purpose pulse drive.

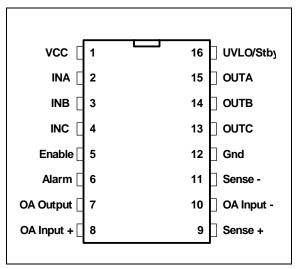


ORDER CODE

Part Number	Temperature Range	Package		
l ait Number	Temperature ivalige	N	D	
TD310I	-40°C, +125°C	•	•	

N = Dual in Line Package (DIP)
D = Small Outline Package (SO) - also available in Tape & Reel (DT)

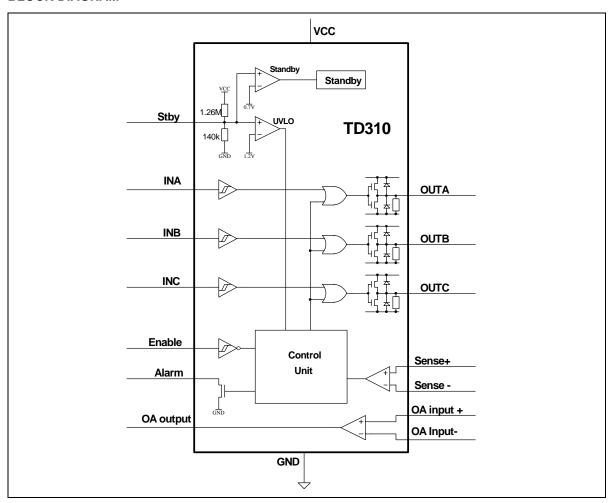
PIN CONNECTIONS (top view)



December 2001 1/9



BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	18	V
V _i	Input Voltage	0 to V _{CC}	V
V _{is}	Sense Input Voltage	-0.3 to V _{CC}	V
T _j	Operating Junction Temperature	-40 to 150	°C
T _{amb}	Operating Ambient Temperature	-40 to 125	°C

OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	4 to 16	V

INSTRUCTION FOR USE

- 1 The TD310 supply voltage must be decoupled with a $1\mu F$ min. capacitor.
- 2 If the application involving TD310 requires maximum output current capability, this current must be pulsed: pulse width 1 μ sec, duty cycle 1% at T_{amb} .

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Distributor of STMicroelectronics: Excellent Integrated System LimitedDatasheet of TD310IDT - IC DRIVER MOS/IGBT TRIPLE 16SOIC

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TD310

ELECTRICAL CHARACTERISTICS

 $V_{CC} = 15V$, $T_{amb} = 25$ °C (unless otherwise specified)

Symbol	mbol Parameter		Тур.	Max.	Unit
I _{cc}	Supply Current with Inputs in High State		1.5	2	mA
LOGIC II	NPUT (all inputs)		•	•	
V _{IH}	High Input Voltage	2			V
V _{IL}	Low Input Voltage			0.8	V
I _{IH}	High Input Current		10		pА
I _{IL}	Low Input Current		10		pА
	Propagation Delay (10% input to 10% output)				
t_{dH} , t_{eL}	Output Delay		200	400	ns
t_{dL} , t_{eH}	Output Delay		60	400	
	$T_{min.} \le Tamb \le T_{max.}$		400		
t _{li}	Input Inhibiting Time		100		ns
t _{dd}	Differential Delay Time Between Channels		20		ns
OUTPUT	DRIVERS	T	1		1
V_{sod}	Sourcing Drop Voltage (A/B/C outputs) I _{source} = 200mA			3	V
V_{sid}	Sinking Drop Voltage (A/B/C outputs) Isink = 200mA			5	V
V_{dem}	Demagnetizing Drop Voltage (A/B/C outputs) Idemag. = 100mA			2	V
R _{opd}	Output Pull Down Resistor		47		kΩ
ALARM	OUTPUT	I	1	1	I
	Low Level Sinking Current		25		Л
I _s	$V_{O} = 0.8V$	5	35		mA
I _{sh}	High Level Sinking Current			1	μΑ
t _A	Alarm Output : Delay Time to Alarm Fall if Sense Input Triggered			500	ns
SENSE I	NPUT	•	•		
V _{ios}	Input Offset Voltage			20	mV
t _{Ai}	Inhibition Time if Sense Input Triggered		1		ms
t _s	Delay Time to Output Fall if Sense Input Triggered All outputs inhibited			600	ns
t _{si}	Inhibition Time of Sense Input		300		ns
V _{shys}	Sense Hysteresis		40		mV
	IONAL AMPLIFIER				I
V _{icm}	Common Mode Input Voltage Range	0 1	to V _{CC} ⁺ -	1.5	V
V _{io}	Input Offset Voltage		I	10	mV
GBP	Gain Bandwidth Product		1		MHz
A _{vd}	Open Loop Gain	60	 	 	dB
SR	Slew Rate at Unity Gain ($R_L = 100k\Omega$, $C_L = 100pF$, $V_i = 3 to 7V$)		0.6	 	V/µs
STAND-I			1 0.0	<u> </u>	•/μο
V _{stdby}	Standby Mode Threshold Voltage	0.3		1.1	V
	Standby Mode Supply Current	0.0	30	1.1	μA
I _{stdby}	VOLTAGE LOCKOUT		1 30	L	μА
			1		۸ /\ /
I _{adj}	Under Voltage Level Adjust Current Internal Stop Threshold (without external adjustment)	10.7	1	10.0	μA/V
V _{st1}	, , , , , , , , , , , , , , , , , , , ,	10.7	0.0	13.3	V
V_{hys}	Threshold Hysteresis		0.8		V

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Datasheet of TD310IDT - IC DRIVER MOS/IGBT TRIPLE 16SOIC

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TD310

UVLO/stdby pin functioning modes

Due to the wide supply voltage range of the TD310, the UVLO function (Under Voltage Lock Out) is externally adjustable by a resistor bridge.

The bridge rate can be calculated in relation with the expected UVLO protection level as follows:

$$V_{UVLO} \times \frac{R1}{R1 + R2} = 1.2V$$
 (where R1 is the lower resistor of the bridge)

The internal resistor sets the default UVLO value to 12V (*) and might influence the external bridge rate if the values of the external resistors are too high. Moreover, the internal resistor ratio is accurate, but the the tolerance on the absolute value of each internal resistor (typically 140k and 1.26M) is about +/-20%. If an external bridge is used, we recommend to choose resistor values not greater than 10k.

The standby threshold value depends of the UVLO value as follows:

$$V_{stdbv} = {0.7}/{1.2} V_{UVLO}$$

Both UVLO and stdby functions can be inhibited by connecting the UVLO/stdby pin to V_{CC}^{+} via a pull up resistor (ex 150k Ω).

The following table summarizes the functions of the TD310:

	Pin	16	9/11	5	2/3/4	15/14/13	6	7/8/10	Con-
	Config	UVLO/ stdby	Sense+/ Sense-	Enable	In A/B/C	Out A/B/C	Alarm	Op-Amp	sumption
			+>-	Х	Х	L	L		
Normal	1	Н	+<-	Н	IN	ĪN	Н	OK	H (1.5mA)
			7 .	L	Х	L	11		(11011111)
Stdby	2	ı	+>-	Х	Х	ı	L	HZ	L
Stuby	2	L	+ < -	^	^	L	Н	112	(30µA)
UVLO	3	М	Х	Х	Х	L	L	OK	Н

Configuration 1: UVLO/stdby = H

The TD310 is in a normal consumption state (1.5mA), the operational amplifier is normally functioning and the buffer outputs are determined by the sense comparator inputs, the enable inputs and the buffer inputs.

Configuration 2: UVLO/stdby = L

The TD310 is in a low consumption state (standby mode $30\mu A$), the buffer outputs are set to low state and the operational amplifier is in high impedance state.

Configuration 3: UVLO/stdby = M

The VCC supply voltage is between VUVLO and Vstdby (**). The TD310 remains in a normal consumption state and the operational amplifier is normally functioning but the buffer outputs and the alarm pin are set to low state.

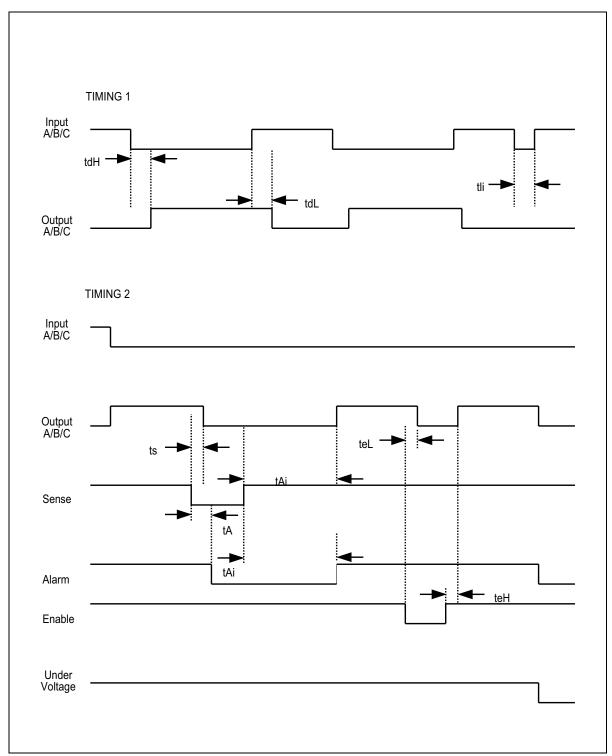
(*) If the UVLO level remains unadjusted, it is recommended to bypass the UVLO/stdby pin with a 1nF capacitor.

(**) If the supply voltage falls below V_{stdby} , the TD310 is set in standby mode (configuration 2).

A



TIMING DIAGRAM

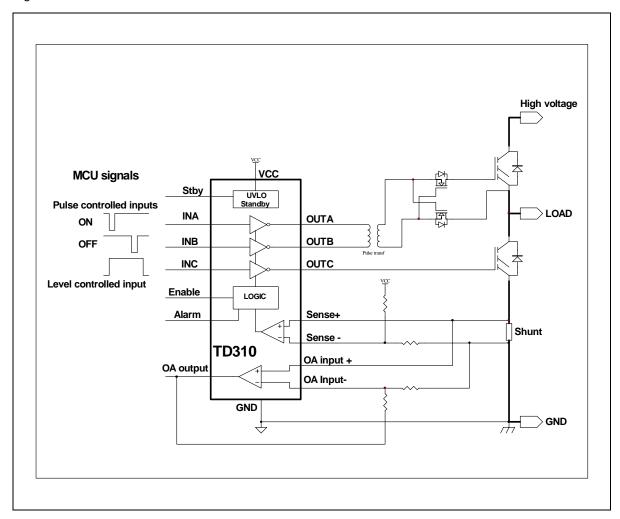






TYPICAL APPLICATIONS

Figure 1: HALF BRIDGE DRIVE IN THREE PHASE MOTOR SYSTEM



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Figure 2: THREE PHASE MOTOR LOW SIDE DRIVE

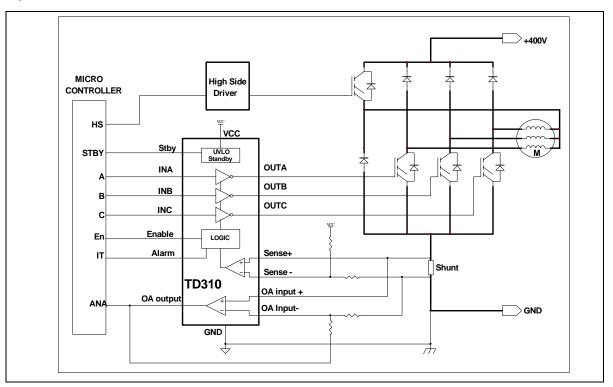
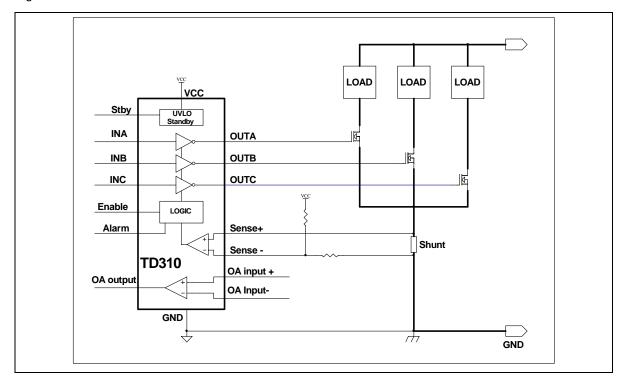


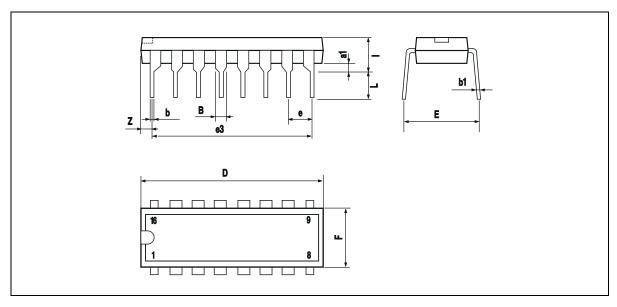
Figure 3 : LOW SIDE DRIVE





PACKAGE MECHANICAL DATA

16 PINS - PLASTIC DIP



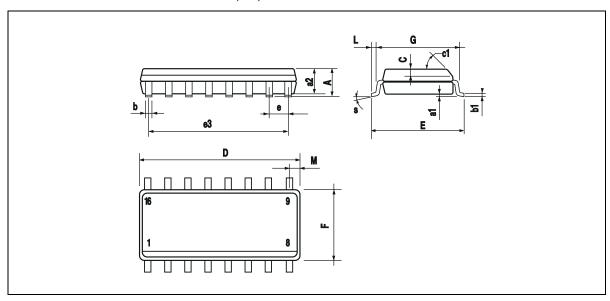
Dim.		Millimeters		Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
a1	0.51			0.020			
В	0.77		1.65	0.030		0.065	
b		0.5			0.020		
b1		0.25			0.010		
D			20			0.787	
E		8.5			0.335		
е		2.54			0.100		
e3		17.78			0.700		
F			7.1			0.280	
i			5.1			0.201	
L		3.3			0.130		
Z			1.27			0.050	

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PACKAGE MECHANICAL DATA

16 PINS - PLASTIC MICROPACKAGE (SO)



Dim		Millimeters		Inches				
Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.		
Α			1.75			0.069		
a1	0.1		0.2	0.004		0.008		
a2			1.6			0.063		
b	0.35		0.46	0.014		0.018		
b1	0.19		0.25	0.007		0.010		
С		0.5			0.020			
c1			45°	(typ.)		•		
D	9.8		10	0.386		0.394		
E	5.8		6.2	0.228		0.244		
е		1.27			0.050			
e3		8.89			0.350			
F	3.8		4.0	0.150		0.157		
G	4.6		5.3	0.181		0.209		
L	0.5		1.27	0.020		0.050		
М			0.62			0.024		
S	8° (max.)							

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